

Obsolete. Alternative is BSS123.

## ZXM41N10F

### SOT23 N-CHANNEL ENHANCEMENT MODE VERTICAL D MOSFET

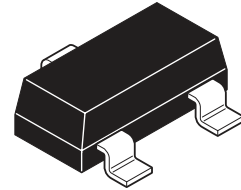
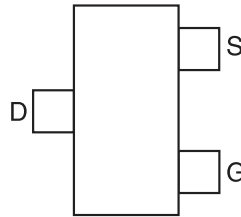
#### FEATURES

- $BV_{DSS} = 100V$

- Low Threshold

#### DEVICE MARKING

- 410



#### ABSOLUTE MAXIMUM RATINGS

PINOUT TOP VIEW

SOT23

PARAMETER	SYMBOL	VALUE	UNIT
Drain-source voltage	$V_{DS}$	100	V
Drain-gate voltage	$V_{DGR}$	100	V
Continuous drain current at $T_{amb}=25^{\circ}C$	$I_D$	170	mA
Pulsed drain current	$I_{DM}$	680	mA
Gate-source voltage	$V_{GS}$	$\pm 20$	V
Power dissipation at $T_{amb}=25^{\circ}C$	$P_{tot}$	360	mW
Operating and storage temperature range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

#### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Drain-source breakdown voltage	$BV_{DSS}$	100			V	$I_D=0.25mA, V_{GS}=0V$
Gate-source threshold voltage	$V_{GS(th)}$	0.5		1.5	V	$I_D=1mA, V_{DS}=V_{GS}$
Gate-body leakage	$I_{GSS}$			50	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Zero gate voltage drain current	$I_{DSS}$			500	nA	$V_{DS}=100V, V_{GS}=0V$
Static drain-source on-state resistance <sup>(1)</sup>	$R_{DS(on)}$			8 12	$\Omega$	$V_{GS}=4.5V, I_D=150mA$ $V_{GS}=3V, I_D=50mA$
Forward transconductance <sup>(1)(2)</sup>	$g_{fs}$	80			mS	$V_{DS}=25V, I_D=100mA$
Input capacitance <sup>(2)</sup>	$C_{iss}$		25		pF	$V_{DS}=25V, V_{GS}=0V, f=1MHz$
Common source output capacitance <sup>(2)</sup>	$C_{oss}$		9		pF	
Reverse transfer capacitance <sup>(2)</sup>	$C_{rss}$		4		pF	
Turn-on delay time <sup>(2)(3)</sup>	$t_{d(on)}$		10		ns	$V_{DD}=30V, I_D=280mA$
Rise time <sup>(2)(3)</sup>	$t_r$		10		ns	
Turn-off delay time <sup>(2)(3)</sup>	$t_{d(off)}$		15		ns	
Fall time <sup>(2)(3)</sup>	$t_f$		25		ns	

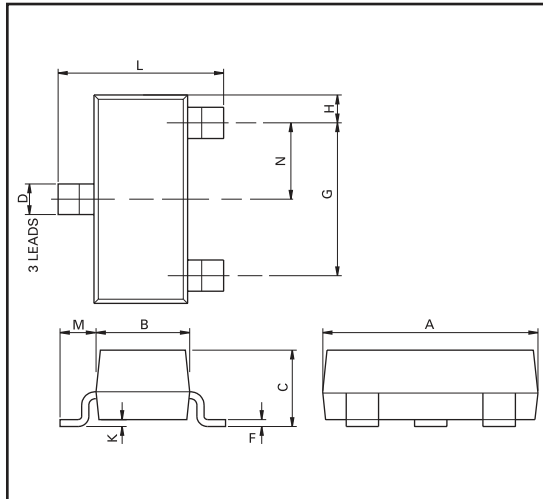
#### NOTES:

<sup>(1)</sup> Measured under pulsed conditions. Width=300 $\mu$ s. Duty cycle  $\leq$ 2% <sup>(2)</sup> Sample test.

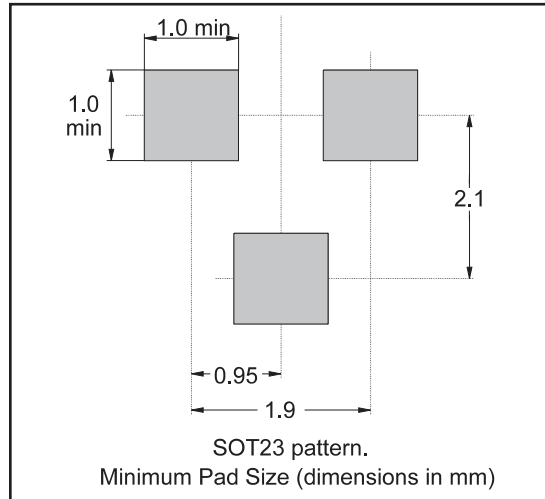
<sup>(3)</sup> Switching times measured with 50 $\Omega$  source impedance and <5ns rise time on a pulse generator

# ZXM41N0F

## PACKAGE OUTLINE



## PAD LAYOUT DETAILS



Controlling dimensions are in millimeters. Approximate conversions are given in inches

## PACKAGE DIMENSIONS

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Max	Max
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	—	1.10	—	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		Θ	10° TYP		10° TYP	

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